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Kind regards,

Team Nexperia



# BCV61

# NPN general-purpose double transistors Rev. 04 — 18 December 2009

Product data sheet

#### 1. **Product profile**

### 1.1 General description

NPN general-purpose double transistors in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview** 

Type number	Package		PNP complement	
	NXP	JEITA		
BCV61	SOT143B	-	BCV62	
BCV61A			BCV62A	
BCV61B			BCV62B	
BCV61C			BCV62C	

#### 1.2 Features

- Low current (max. 100 mA)
- Low voltage (max. 30 V)
- Matched pairs

#### 1.3 Applications

- Applications with working point independent of temperature
- Current mirrors

#### **Pinning information** 2.

Table 2 Pinning

Table 2.	riiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	collector TR2; base TR1 and TR2	4 3	4 3
2	collector TR1		XI 17
3	emitter TR1		TR2
4	emitter TR2	1 2	1 2 006aaa842



#### NPN general-purpose double transistors

# 3. Ordering information

Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
BCV61	<b>-</b>	plastic surface-mounted package; 4 leads	SOT143B				
BCV61A							
BCV61B							
BCV61C							

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BCV61	1M*
BCV61A	1J*
BCV61B	1K*
BCV61C	1L*

<sup>[1] \* = -:</sup> made in Hong Kong

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	istor				
$V_{CBO}$	collector-base voltage	open emitter	-	30	V
$V_{CEO}$	collector-emitter voltage	open base	-	30	V
$V_{EBS}$	emitter-base voltage	$V_{CE} = 0 V$	-	6	V
I <sub>C</sub>	collector current		-	100	mA
I <sub>CM</sub>	peak collector current		-	200	mA
$I_{BM}$	peak base current		-	200	mA
Per devic	ee				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[1] -	250	mW
Tj	junction temperature		-	150	°C
$T_{amb}$	ambient temperature		-65	+150	°C
$T_{stg}$	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB).

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

#### NPN general-purpose double transistors

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB.

## 7. Characteristics

Table 7. Characteristics

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Transist	or TR1					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 30 \text{ V};$ $I_{E} = 0 \text{ A}$	-	-	15	nA
		$V_{CB} = 30 \text{ V};$ $I_{E} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$	-	-	5	μА
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V};$ $I_C = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V};$ $I_{C} = 100  \mu\text{A}$	100	-	-	
		$V_{CE} = 5 \text{ V};$ $I_{C} = 2 \text{ mA}$	110	-	800	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$	-	90	250	mV
		$I_C = 100 \text{ mA};$ $I_B = 5 \text{ mA}$	-	200	600	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$	[1] -	700	-	mV
		$I_C = 100 \text{ mA};$ $I_B = 5 \text{ mA}$	[1] -	900	-	mV
$V_{BE}$	base-emitter voltage	$I_C = 2 \text{ mA};$ $V_{CE} = 5 \text{ V}$	[2] 580	660	700	mV
		$I_C = 10 \text{ mA};$ $V_{CE} = 5 \text{ V}$	[2] _	-	770	mV
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V};$ $I_{C} = 10 \text{ mA};$ $f = 100 \text{ MHz}$	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	2.5	-	pF
NF	noise figure	$V_{CE} = 5 \text{ V};$ $I_{C} = 200  \mu\text{A};$ $R_{S} = 2  k\Omega;$ $f = 1  k\text{Hz};$ $B = 200 \text{ Hz}$	-	-	10	dB

#### **NPN** general-purpose double transistors

**Table 7.** Characteristics ... continued  $T_i = 25$  °C unless otherwise specified.

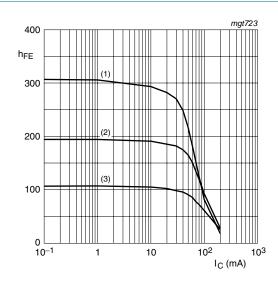
,	a amee care mee speemea.		_				
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Transist	or TR2						
$V_{EBS}$	emitter-base voltage	$V_{CB} = 0 \text{ V};$ $I_E = -250 \text{ mA}$		-	-	-1.8	V
		$V_{CB} = 0 \text{ V};$ $I_E = -10  \mu\text{A}$		-400	-	-	mV
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V};$ $I_C = 2 \text{ mA}$					
	BCV61			110	-	800	
	BCV61A			110	-	220	
	BCV61B			200	-	450	
	BCV61C			420	-	800	
Transist	ors TR1 and TR2						
$I_{C1}/I_{E2}$	current matching	$I_{E2} = -0.5 \text{ mA};$ $V_{CE1} = 5 \text{ V}$					
		T <sub>amb</sub> ≤ 25 °C		0.7	-	1.3	
		T <sub>amb</sub> ≤ 150 °C		0.7	-	1.3	
I <sub>E2</sub>	emitter current 2	V <sub>CE1</sub> = 5 V	[3]	-	-	-5	mA

<sup>[1]</sup>  $V_{BEsat}$  decreases by about 1.7 mV/K with increasing temperature.

<sup>[2]</sup>  $V_{BE}$  decreases by about 2 mV/K with increasing temperature.

<sup>[3]</sup> Device, without emitter resistors, mounted on an FR4 PCB.

#### NPN general-purpose double transistors



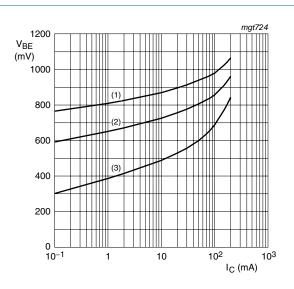
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \,^{\circ}C$$

Fig 1. BCV61A: DC current gain as a function of collector current; typical values



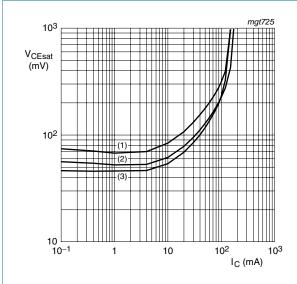
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 2. BCV61A: Base-emitter voltage as a function of collector current; typical values



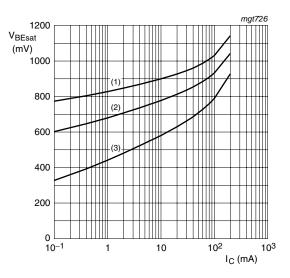
$$I_{\rm C}/I_{\rm B}=20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 3. BCV61A: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

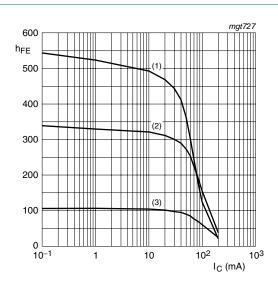
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 4. BCV61A: Base-emitter saturation voltage as a function of collector current; typical values

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#### NPN general-purpose double transistors



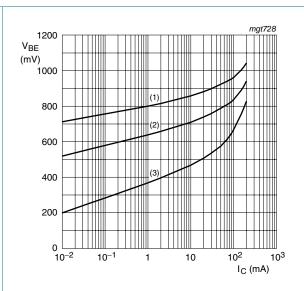
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \,^{\circ}C$$

Fig 5. BCV61B: DC current gain as a function of collector current; typical values



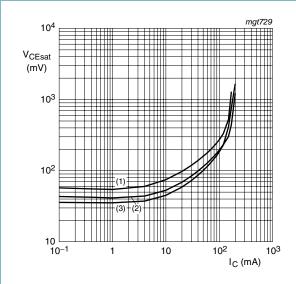
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 6. BCV61B: Base-emitter voltage as a function of collector current; typical values



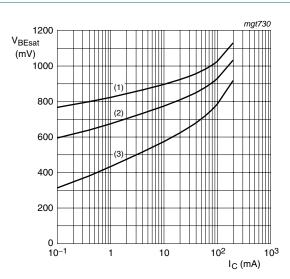
$$I_{\rm C}/I_{\rm B}=20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. BCV61B: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

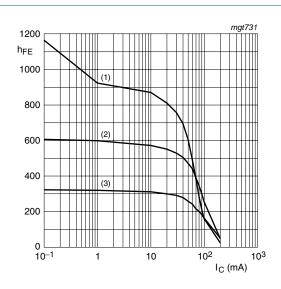
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 8. BCV61B: Base-emitter saturation voltage as a function of collector current; typical values

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#### NPN general-purpose double transistors



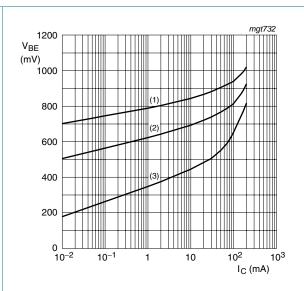
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \,^{\circ}C$$

Fig 9. BCV61C: DC current gain as a function of collector current; typical values



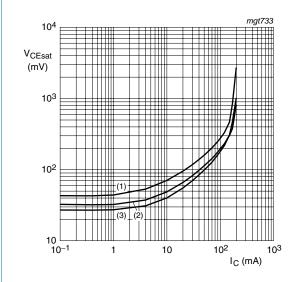
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. BCV61C: Base-emitter voltage as a function of collector current; typical values



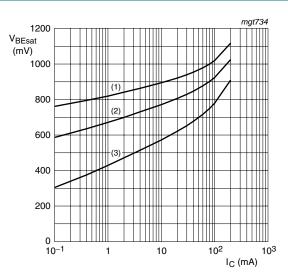
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. BCV61C: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

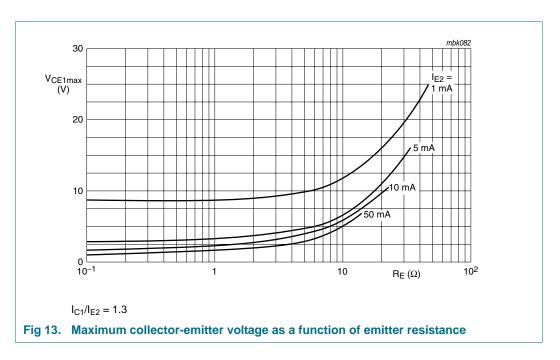
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

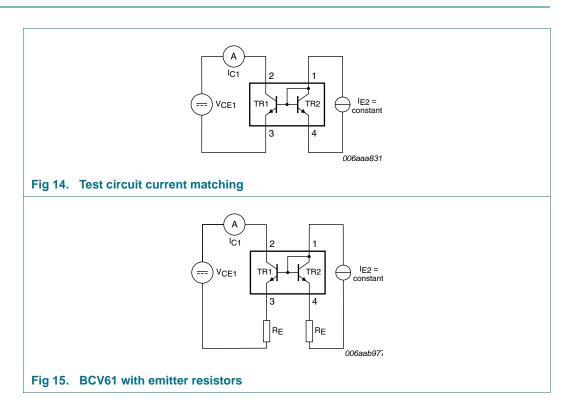
(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 12. BCV61C: Base-emitter saturation voltage as a function of collector current; typical values

#### NPN general-purpose double transistors

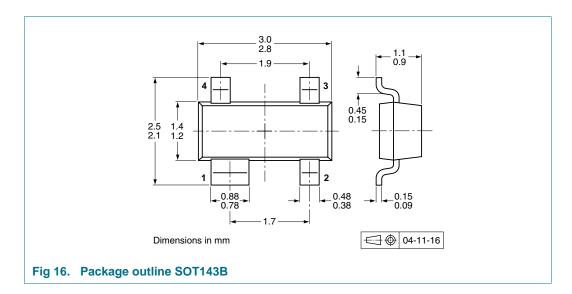


## 8. Test information



#### NPN general-purpose double transistors

# 9. Package outline



# 10. Packing information

Table 8. Packing methods

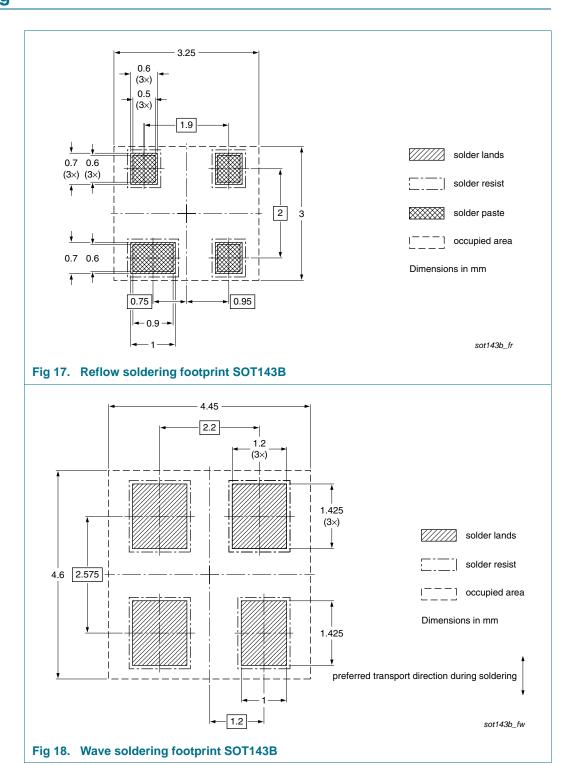
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity		
			3000	10000		
BCV61	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235		
BCV61A						
BCV61B						
BCV61C	_					

<sup>[1]</sup> For further information and the availability of packing methods, see <u>Section 14</u>.

#### NPN general-purpose double transistors

# 11. Soldering



## NPN general-purpose double transistors

# 12. Revision history

#### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BCV61_4	20091218	Product data sheet	-	BCV61_3	
Modifications:		of this data sheet has been re	designed to comply w	vith the new identity	
	<ul> <li>Legal texts h</li> </ul>	ave been adapted to the nev	v company name whe	re appropriate.	
	<ul> <li>Section 3 "O</li> </ul>	rdering information": added			
	<ul> <li>Section 4 "Marking": updated</li> </ul>				
	• Figure 1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11 and 12: added				
	Section 8 "Test information": added				
	• <u>Figure 16</u> : su	uperseded by minimized pacl	kage outline drawing		
	<ul> <li>Section 10 "F</li> </ul>	Packing information": added			
	Section 11 "Soldering": added				
	<ul> <li>Section 13 "I</li> </ul>	<u>_egal information"</u> : updated			
BCV61_3	19990408	Product specification	-	BCV61_CNV_2	
BCV61_CNV_2	19970616	Product specification	-	-	
-					

#### NPN general-purpose double transistors

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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#### **NPN** general-purpose double transistors

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Date of release: 18 December 2009 Document identifier: BCV61\_4

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